

SANYO

No. 4740

STK730-080**Self-Excitation Type Semi-Regulated
Switching Regulator (210 W Output)****Overview**

The STK730-080 provides on-chip the power switching, error detection, amplifier, and overcurrent protection circuits required in a self-excitation type semi-regulated switching regulator. As a result, it can be used to construct a switching power supply with a minimal number of external components. Furthermore, due to the adoption of MOSFETs as the power switching elements, an oscillator frequency higher than that possible with bipolar transistors can be used. This allows miniaturized power supply systems to be constructed by reducing the size of the pulse transformer and capacitors.

Applications

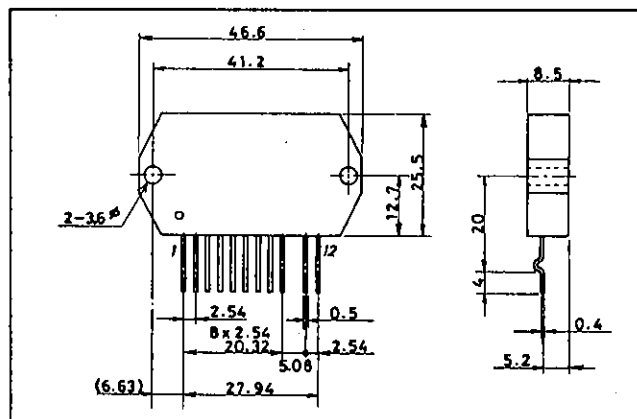
- Power supplies in CRT and CTV products
- Power supplies in office automation products
- Switching power supplies in general

Features

- Power MOSFETs adopted
- Built-in error detection circuit
- Built-in overcurrent protection circuit
- Product series differentiated by output capacity (110 to 280 W)
- Few external components required
- Since the STK730-080 supports higher oscillator frequencies, smaller pulse transformers can be used.
- Takes all major national stability standards and EMF hazard standards into consideration.
- The IMST (insulated metal substrate technology) substrate functions as an EMF shield plate and supports low noise design.

Package Dimensions

unit: mm

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Specifications

Maximum Ratings at $T_a = 25^\circ\text{C}$ ($T_c = 25^\circ\text{C}$ unless specified otherwise)

Parameter	Symbol	Condition	Rating	Unit
Operating substrate temperature	$T_c \text{ max}$	*1	115	$^\circ\text{C}$
AC input voltage	V_{AC}	*2	280	Vrms
Operating temperature	T_{opr}		-10 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}		-30 to +115	$^\circ\text{C}$
Maximum output power	$W_o \text{ max}$	*2 When $V_O = 135 \text{ V}$	210	W
[TR1]				
Drain current	I_D	*3	6	A
Pulse drain current	$I_D \text{ (puls)}$	*3	15	A
Drain reverse current	I_{DR}		6	A
Gate-source voltage	V_{GSS}		± 30	V
Allowable power dissipation	P_d		100	W
Chip junction temperature	$T_J \text{ max}$		150	$^\circ\text{C}$
Thermal resistance	θ_{j-c}		1.25	$^\circ\text{C/W}$
[ZD1]				
Allowable power dissipation	P_{ZD1}		500	mW
Chip junction temperature	$T_J \text{ (ZD1) max}$		125	$^\circ\text{C}$
Thermal resistance	$\theta_{j-c} \text{ (ZD1)}$		0.2	$^\circ\text{C/mW}$

Note: 1. The recommended substrate temperature is 105°C (maximum).
 2. In the specified test circuit
 3. See the ASO characteristics for these values in overcurrent states.

Recommended Operating Conditions at $T_a = 25^\circ\text{C}$

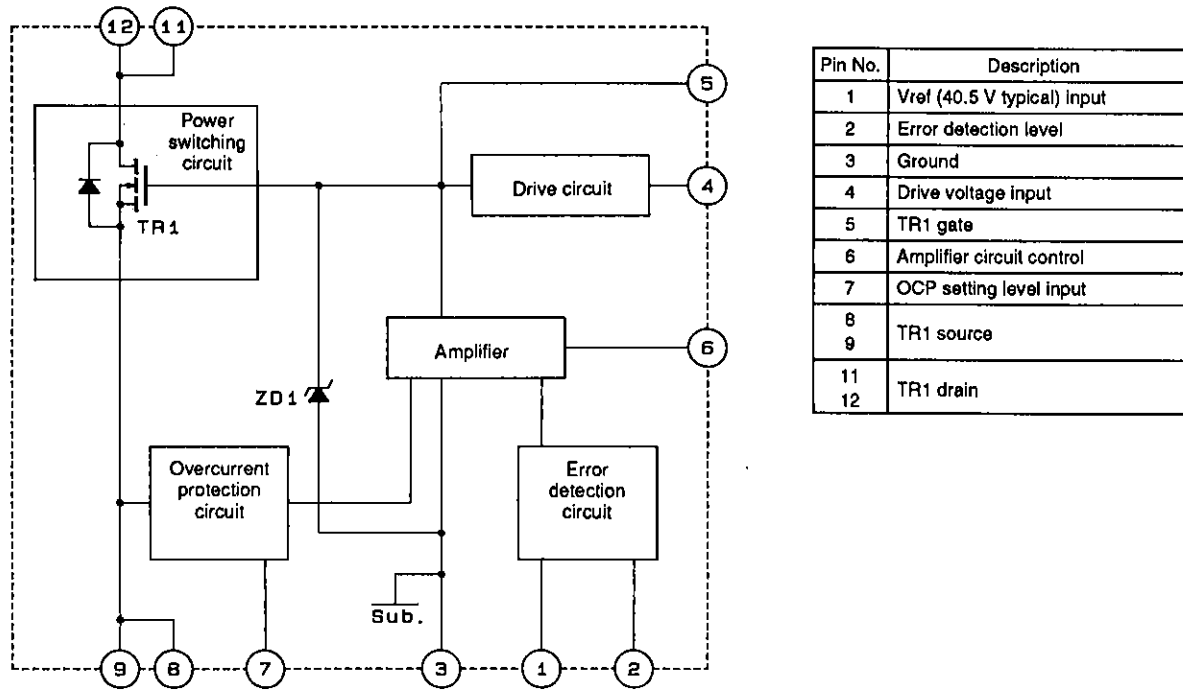
Parameter	Symbol	Condition	Rating	Unit
Pin 4 input voltage	V_4		± 8 to ± 24	V
Oscillator frequency	f_{osc}		20 to 120	kHz

Operating Characteristics at $T_a = 25^\circ\text{C}$ ($T_c = 25^\circ\text{C}$ unless specified otherwise)

Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Output voltage setting		* $I_{in} = 8 \text{ mA}$	40.0	40.5	41.0	V
Output voltage temperature coefficient		* $T_c = 0 \text{ to } +105^\circ\text{C}$, $I_{in} = 8 \text{ mA}$		7		mV/ $^\circ\text{C}$
[TR1]						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10 \text{ mA}$, $V_{GS} = 0 \text{ V}$	900			V
Gate-source cutoff voltage	$V_{GS} \text{ (off)}$	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$	2.0		3.0	V
On resistance	$R_{DS} \text{ (on)}$	$I_D = 3 \text{ A}$, $V_{GS} = 10 \text{ V}$		2.0	3.0	Ω
Input capacitance	C_{iss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		1200		pF
[ZD1]						
Zener voltage	V_Z	$I_Z = 5 \text{ mA}$	23.7		26.3	V

Note: * In the specified test circuit

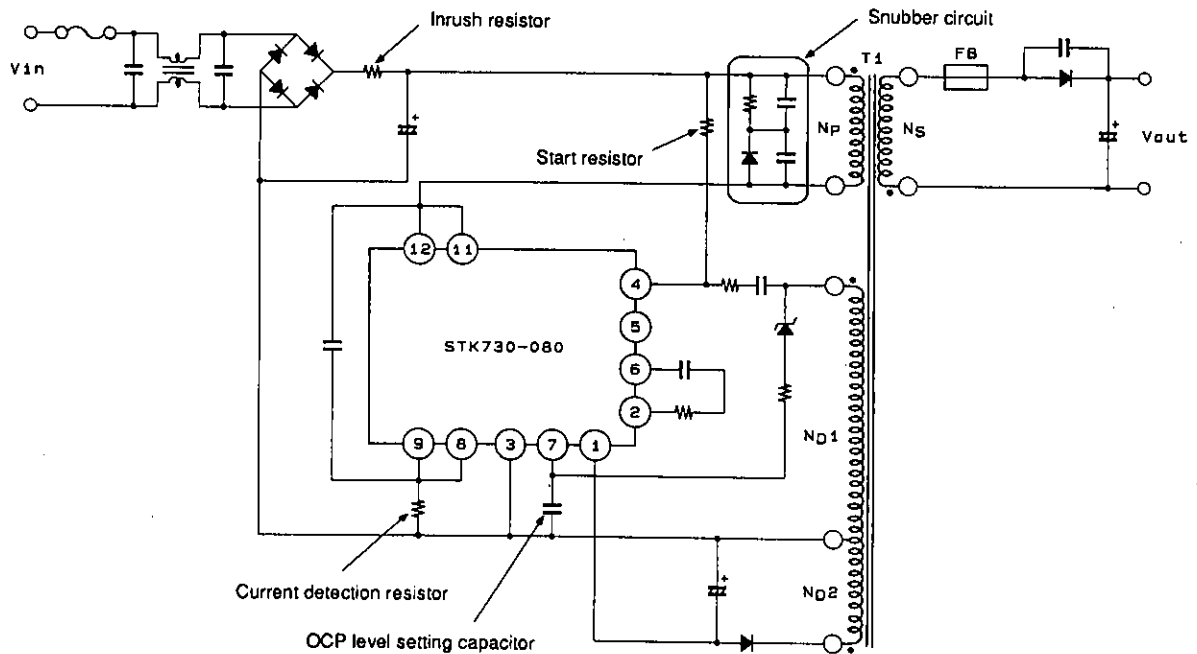
Equivalent Circuit Block Diagram



A01842

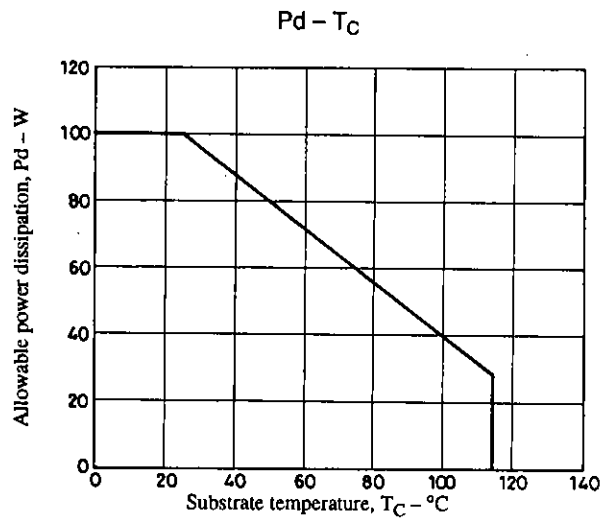
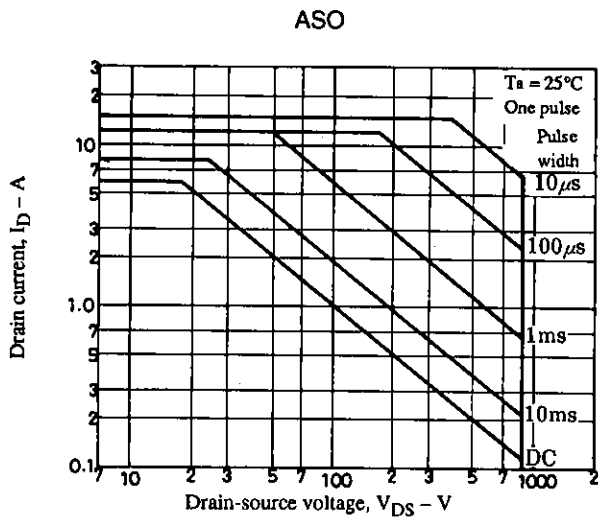
Note: The back surface of the IC is not an insulator, and may be shorted to pin 3.

Application Circuit Example



A01843

Characteristics Data



Series Organization

These products are provided as a product series whose members differ mainly in their power capacity.

Note that the following table includes products that are under development. Contact your Sanyo sales representative for information on product availability.

Product No.	Maximum Rating					Operating Characteristic		
	V_{DS}	T_{stg}^*	$T_C \text{ max}$	$T_J \text{ max}$	I_D	AC input range	$W_o \text{ max}$	$R_{on \text{ typ.}}$
	V	$^\circ\text{C}$	$^\circ\text{C}$	$^\circ\text{C}$	A	V	W	Ω
STK730-010	500	-30 to +115	+115	+150	6.0	85 to 132	110	1.4
STK730-020					8.0		145	0.8
STK730-030					10.0		180	0.7
STK730-040					12.0		210	0.55
STK730-050					15.0		280	0.3
STK730-060	900	-30 to +115	+115	+150	3.0	170 to 264	110	5.0
STK730-070					5.0		180	3.0
STK730-080					6.0		210	2.0
STK730-090					8.0		280	1.2

Note: * The recommended substrate temperature is 105°C (maximum).

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